

IN THE SPECIFICATION

On page 11, at lines 1, 4, and 20, change "gate area 510" to read "gate region 510". On page 11, at line 2 change "gate area 110" to read "gate region 110". A replacement copy in clean form of the two affected paragraphs, starting at page 10, line 21, and extending to page 11, line 15, is as follows:

In one embodiment of the present invention, the shifting of the location of the flat band by about 0.48 volts may be accomplished by the use of the PMOS transistor 500 of Figure 5. In order to move the flat band magnitude from about 1.5 volts to about 1.98 volts, a change of about 0.48 volts, one embodiment changes the threshold voltage V_t by changing the work function of the material comprising the gate region 510. The p+ poly-silicon gate region 110, which has a work function of approximately - 0.56 volts, is replaced by a p+ platinum-silicide gate region 510, which has a work function of approximately - 1.04 volts.

In alternate embodiments, other gate materials such as tantalum nitrate (TaN), iridium (Ir), nickel (Ni), or arsenic (As) may be used to obtain different flat band voltages, depending upon the magnitude of the voltage to be decoupled. These materials may be used by themselves or as dopants in silicon, poly-silicon, or other materials. In further embodiments, the flat band magnitude may be changed by changing the dopant levels of substrate 502 and channel area 508. Finally, in alternate embodiments when V_{cc} differs from 0.4 volts, a